**Fig. 1**

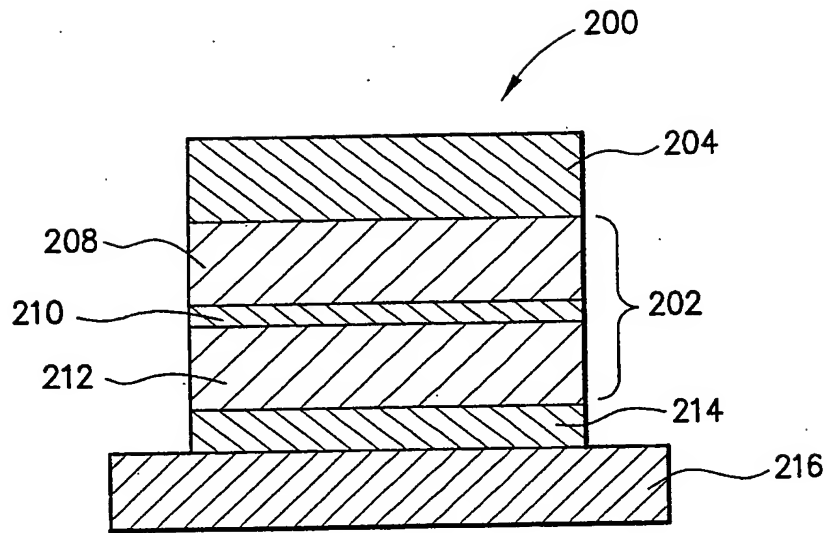


Fig. 2

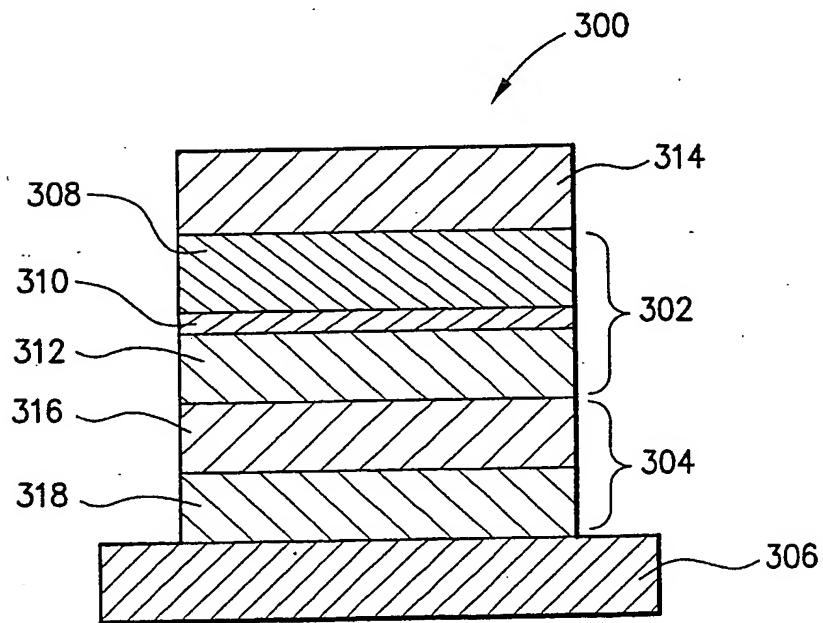


Fig. 3

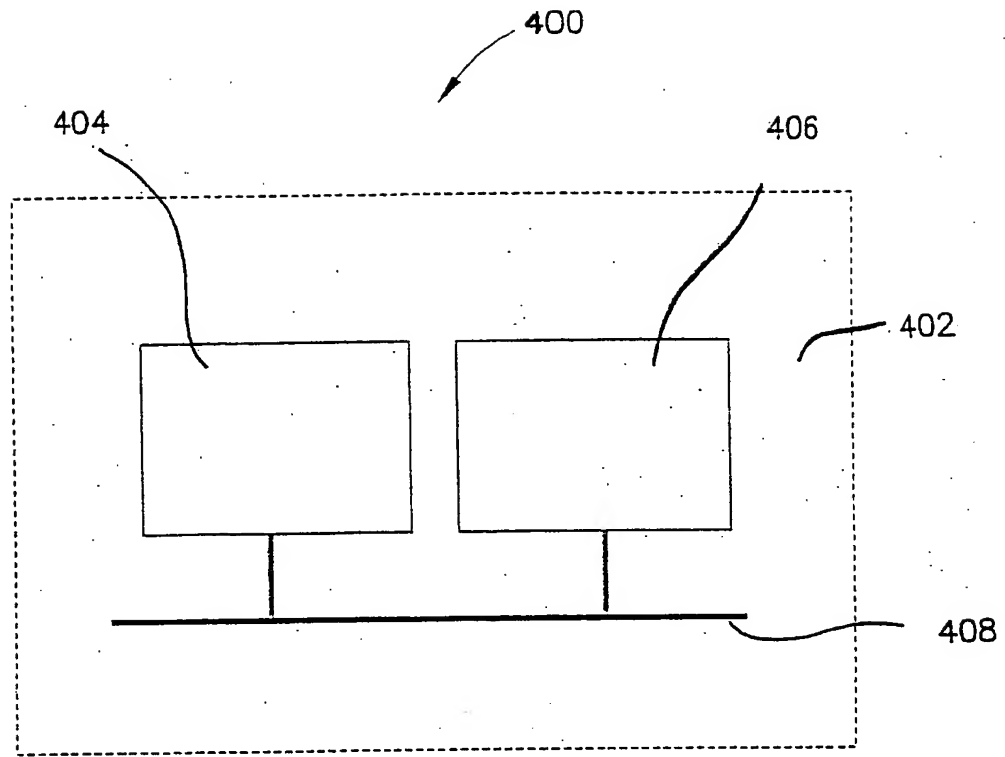


Fig. 4

500

HEATING MRAM CELLS OF AN ARRAY OF MRAM CELLS SWITCHABLE BETWEEN TWO STATES UNDER THE INFLUENCE OF A MAGNETIC FIELD, EACH MRAM CELL COMPRISING A REFERENCE LAYER AND A DATA LAYER, THE REFERENCE LAYER HAVING A LOWER COERCIVITY THAN THE DATA LAYER

502

UTILIZING THE GENERATED HEAT TO REDUCE THE COERCIVITY OF THE REFERENCE LAYER AND FACILITATE SWITCHING OF THE REFERENCE LAYER

504

Fig. 5